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(54) **Title:** MEASUREMENT OF STITCHING ERROR USING SPLIT TARGETS

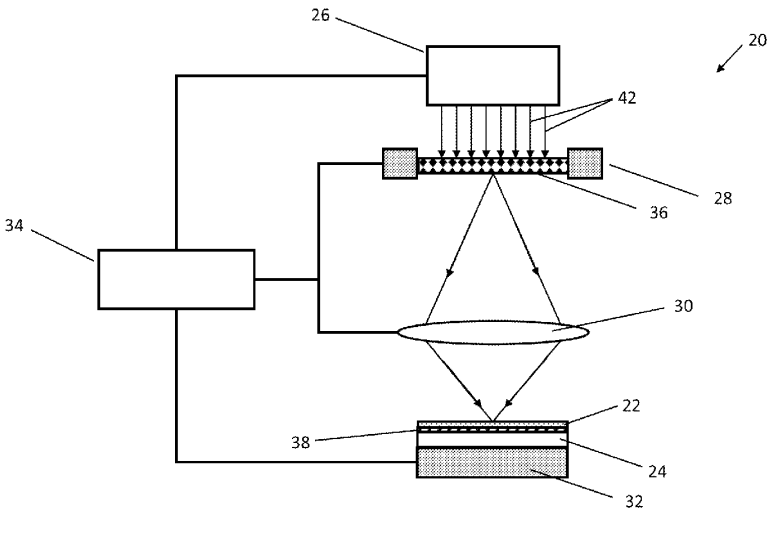

Fig. 1

(57) **Abstract:** A method of semiconductor metrology includes patterning a film layer on a semiconductor substrate to define a first field on the semiconductor substrate with a first pattern comprising at least a first target feature within a first margin along a first edge of the first field and to define a second field, which abuts the first field, with a second pattern comprising at least a second target feature within a second margin along a second edge of the second field, such that the second edge of the second field adjoins the first edge of the first field. The first target feature in the first margin is adjacent to the second target feature in the second margin without overlapping the second target feature. An image is captured of at least the first and second target features and is processed to detect a misalignment between the first and second fields.

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